

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

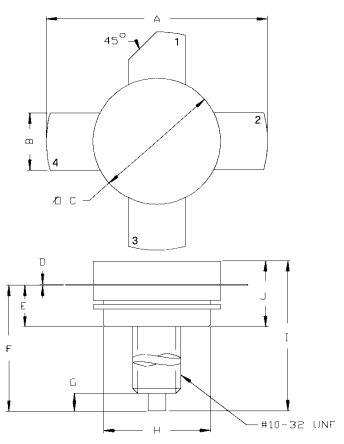
The **TPV375** is a Common Emitter Device Designed for Class A Television Band III Applications.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	8 A
V_{CB}	65 V
P_{DISS}	140 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
q_{JC}	1.5 °C/W

PACKAGE STYLE .500 4L STUD		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
	A	1.010/25.65
	B	.220/5.59
	C	.495/12.57
	D	.003/0.08
	E	.160/4.06
	F	.622/15.80
	G	.100/2.54
	H	.415/10.54
	I	.720/18.29
	J	.250/6.35
		.290/7.37

ORDER CODE: ASI10760

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	35			V
BV_{CER}	I _C = 50 mA R _{BE} = 10 Ω	60			V
BV_{CBO}	I _C = 50 mA	65			V
BV_{EBO}	I _E = 10 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	20		120	---
C_{ob}	V _{CB} = 30 V f = 1.0 MHz			85	pF
G_{PE} y	V _{CE} = 28 V I _C = 2.5 A P _{out} = 20 W	8.0	9.0		---
	f = 225 MHz VSWR = ∞:1	NO DEGRADATION IN OUTPUT POWER			
IMD₃	V _{CE} = 28 V I _C = 2.5 A P _{ref} = 14 W f = 225 MHz Vision = -8.0 dB Snd. = -7.0 dB SB = -16 dB			-55	dB



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